E ect of an electric eld on a oating lipid bilayer: a neutron re ectivity study

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We present here a neutron relectivity study of the in uence of an alternative electric eld on a supported phospholipid double bilayer. We report for the rst time a reproducible increase of the uctuation amplitude leading to the complete unbinding of the oating bilayer. Results are in good agreement with a semi-quantitative interpretation in terms of negative electrostatic surface tension.

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I. IN TRODUCTION

In an aqueous environment, phospholipids self-assemble into bilayers; these 2D systems have been recently extensively studied, as they display complex peculiar behaviours [1, 2], and constitute the major component of the cell membrane [3]. The strong in uence of electric elds on lipid bilayers is interesting both from a fundamental point of view and for practical aspects, and has consequently received an important research e ort. Large electric elds are also used to introduce macrom olecules in vesicles or cells by formation of long-lived pores in the bilayers [4, 5], and also by endocytocis [6]. Smaller alternative electric elds are commonly used to destabilise lipid bilayers in order to form large unilamellar vesicles [7, 8] in the so called electroformation technique. Recently Burgess et al. [9] have studied the e ect of a static electric eld (surface charge) on the structure of supported bilayers.

A lineage it is a widely used technique, the mechanism involved in vesicle electroform ation is not well understood yet. In a recent theoretical paper [10], Sens and Isam bert have suggested that a "negative surface tension" due to the electric eld induces an undulation instability of the bilayer, and that hydrodynam ical elects select the fastestdestabilised mode. These predictions are di cult to test in classical electroform ation experiments. As a matter of fact, the initial system is usually a rather disordered lam ellar phase, obtained by hydration of a dry lipid lm and, consequently, the result is very polydisperse in both size and degree of lam ellar order. Recently, Constantin et al. [11] have reported the list study of membrane destabilisation by an electric eld on a more controlled system : a solid-supported fully-hydrated oriented lam ellar phase (from 10 to 3000 bilayers). They observed for the list time individual peeling of the bilayers, but were not able to con list or refute the existence of electrodynam ical instability.

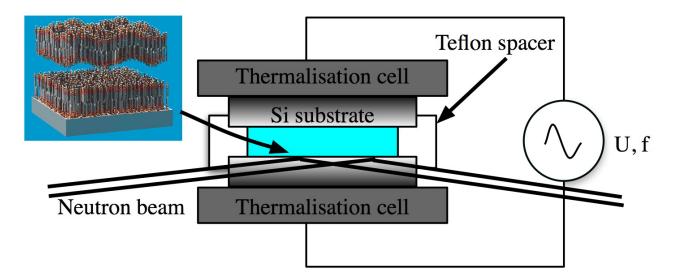


FIG. 1: Experim ental set-up: the two identical silicon substrates (10 mm -thick) are in therm al and electrical contact with therm alisation blocks. The PTFE spacer ensures a 5 mm separation between the two blocks.

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B ecause they are quite free of defects, double bilayer system s are promising candidates to reach better understanding of the mechanism of vesicle formation in a well-de ned geometry. Recent work has shown that they enable local study of the destabilisation of a single mem brane [12]. In this paper we focus on the steps of the bilayer destabilisation by an electric eld as detected by neutron re ectivity.

II. MATERIALS AND METHODS

A. Sam ple preparation

Supported single and double-bilayers of DPPC and DSPC (1, 2-dipalm itoyl-sn-glycero-3-phosphocholine and 1, 2-distearoyl-sn-glycero-3-phosphocholine, A vantiPolar Lipids) m olecules were prepared using the Langmuir-B lodgett and Langmuir-Schaefer techniques, as described in detail previously [13].

B ilayers were deposited on silicon substrates (highly doped 2-10 $\,$ cm⁻¹, 5 5 1 cm³), polished to produce a high quality crystal surface with rm s. roughness < 0.2 nm (SILTRONIX, Archamps, F). A fler careful cleaning, the silicon blocks were made highly hydrophilic by a UV/ozone treatment as in [13]. Lipid depositions were performed at a constant surface pressure of 40 m N/m, the Langmuir trough (NIMA, W arwick, UK) being therm alised at 20 C. Transfer ratios for the rst layers were always high and of the same order as for samples described in [13]. A very precise adjustment of sample horizontality during the Schaefer dip, crucial for a good quality sample, led to transfer ratios always bigger than 0.96. A fler the deposition of the fourth layer, samples were constantly kept into water. They were closed while submerged in the trough, using a 5 mm -thick-PTFE spacer and a sim ilar silicon substrate as a lid, and then placed into a water-regulated tem perature chamber (see gure I).

A nnealing was generally perform ed by progressively heating the sam ple to the uid phase and then cooling it back to the gelphase. Then after careful caracterisation of the structure in the geland the uid phases, the adopted protocol consisted in applying to the supported uid bilayer(s) an alternative electric eld of xed am plitude, decreasing gradually the frequency (from 200 H z to 5 H z). For each value of the frequency re ectivity data were collected. All m easurem ents were m ade at 62 C to ensure sam ple uidity.

B. Neutron re ectivity: basic principles and measurements

Specular re ectivity, R(q), de ned as the ratio between the specularly re ected and incoming intensities of a neutron beam, is measured as a function of the wave vector transfer, q = 4 sin = perpendicular to the re ecting surface, where is the angle and the wavelength of the incoming beam. R(q) is related to the scattering length density across the interface, (z), by the relation [4]:

$$R (q) = \frac{16^{2}}{q^{2}} j_{\gamma} (q)^{2}$$
(1)

where $j \sim (q) j$ is the one-dimensional Fourier Transform of (z).

Specular re ectivity allows the determ ination of the structure of matter perpendicular to a surface or an interface. Experiments are performed in rection at grazing incidence. Sam plesmust be planar, very at and with roughness as small as possible. D ata were collected at the H igh Flux R eactor (HFR) of the Institut-Laue Langevin (ILL, G renoble, F) both on the small angle di ractom eter D 16 (preliminary measurements) and on the high ux rejectom eter D 17, designed to take advantage of both T in e-O fF light (TOF) and monochromaticm ethods of measuring rejectivity (dual mode instrument) [15, 16]. In this study measurements were all taken with the instrument in the TOF mode by using a spread of wavelengths between 2 and 20 A at two incoming angles (typically 0.7 and 4) and with a resolution, de ned by two choppers, of t=t = 1% and 5%, respectively, where t is the neutron pulse duration. The beam was de ned in the horizontal direction by a set of two slits, one just before the sam ple and one before a vertically focusing guide. Neutron rejectivity from the same sam ple was measured at di erent temperatures monitored with a therm occuple (equilibration time 25 minutes, stability < 0:1 C, absolute precision < 0:3 C), in the water-regulated sam ple chamber already described in [13]. The useful q-range, before hitting the sam ple background, spanned from 0.007 to 0.24 A⁻¹ and was measured in about two hours, also after equilibration. The equilibration time varied depending on the step of tem perature increase or decrease. For a step of 1 C it was of about 15 m inutes.

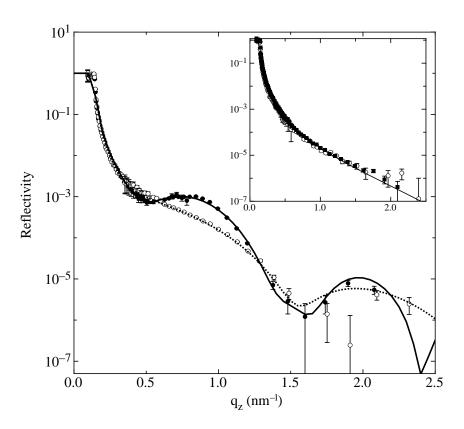


FIG.2: Re ectivity curves: closed circles () = double D SPC bilayer in CaCl before applying electric eld and best twith a double bilayer model (full line); open circles () = after applying a (10 V, 10 Hz) eld and best twith a single bilayer model (dashed line). In insert, re ectivity curves for the bare substrate before and after the experiment (and best twith a silicon oxyde layer model).

C. A nalysis of re ectivity data

Specular re ectivity is a technique able to resolve the stacking of several slabs each one with a certain thickness and a certain scattering length density. D ata analysis requires a good know ledge of the sam ple and here it was done via m odel tting. B om and W olf gave a general solution, the so called optical matrix method [7], to calculate the re ectivity from any number of parallel, hom ogeneous layers, which is particularly useful since any layered structure can be approximately described by dividing it into an arbitrary number of layers parallel to the interface, each having a uniform scattering length density. A re ectivity curve essentially re ects the sam ple density perpendicular to the substrate surface, or rather the square modulus of its Fourier transform. Since the phase is lost, data need to be

tted (e.g. with a slab model) to extract the density pro le. In previous studies [3], multiple contrast neutron measurements have determined within A precision the pro le of adsorbed and oating bilayers, in the gel and the uid phases. Each bilayer is resolved into outer-inner-outer slabs: outer slabs = heads (phosphocholine and glycerol groups), inner slab = tails (hydrocarbon chains). A water lm of thickness D_w separates the adsorbed and oating bilayers. Taking into account the water layer between the adsorbed bilayer and the substrate and the silicon oxide

layer, this leads to 9 slabs in total, each one having its own average thickness and scattering length density. Moreover, each interface between two slabs has a certain width, also called rm s. roughness. Since this enters into the density prole, it can be determined by ts of re ectivity curves, but it is not possible to determine whether it is a static intrinsic width or an average over the neutron beam 's correlation length of tem poral or spatial uctuations.

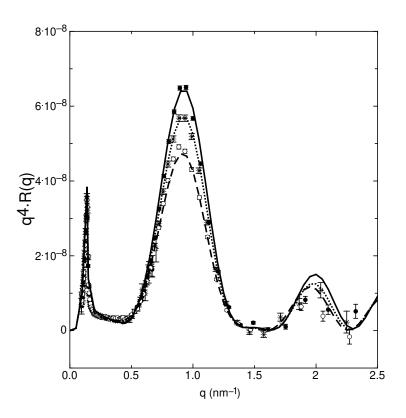


FIG.3: M odi cation of the re ectivity curve with respect to the frequency of the electric eld. A 5V alternative eld is applied to a DSPC double bilayer in D_2O ; full circles () with f= 100 H z; stars (?) with f= 50 H z; open circles () with f= 10 H z. The lines are the best to obtained with the values of the roughness given in the text.

III. RESULTS

A. Complete unbinding in a highly conductive solution

The rst result of this paper is the observation for the rst time of the oating bilayer complete unbinding by application of an electric eld. This e ect was observed on two di erent sam ples under the same conditions: double bilayers of DSPC in a CaCl₂ in D₂O solution (0.35 mM \perp ¹, measured conductivity of 16.62 S cm ¹) at low frequency (10 H z) and for a voltage amplitude higher than 5 V. Figure 2 shows re ectivity data for one of these double bilayer DSPC samples before and after applying the electric eld. The curves correspond to the best ts obtained with a 9-slab m odel and are in good agreement with previous multi-contrast neutron re ectivity experiments [3].

A fier the unbinding we still observed the presence of the rst bilayer, without any major change in structure, but slightly shifted away from the substrate (gure 2). A fier removing the bilayer by cleaning the substrate we could con rm that the silicon oxide layer was unmodiled and therefore that there was no form ation of porous silicon oxide (gure 2 in insert). The adsorbed bilayer might possibly be removed by application of a lower frequency or/and higher voltage eld, but this could not be tested as it could have induced signil cant oxidation of the silicon. As a matter of fact, we had previously been able to determ ine that the form ation of porous silicon oxide is very sudden and occurs when frequency becomes lower than 5 Hz in identical conditions (unpublished data).

B. Progressive increase of uctuations in a poorly conductive solution

1. D ouble bilayer

As this complete unbinding of the oating bilayer is very sudden, we tried to observe previous steps of the destabilisation in a low conductivity electrolyte such as D_2O ($_s^1 = 0.34$ S cm 1). We performed experiments on a DSPC double bilayer in these conditions, and were able to observe a progressive modil cation of the relectivity curves (gure 3).

At high frequencies (f > 100 Hz), this modi cation appeared to be irreversible and involved mainly the rst bilayer: the thin water layer (0.3 nm, see table I) initially separating the substrate and the rst bilayer disappears (or becomes smaller than our experimental resolution), while the amount of solvent in the bilayer increases from 2% to 6%. For this rst con ned bilayer, assuming that the rst water layer behaves as a dielectric, both e ects could originate from the electrostatic pressure acting on the electric silicon oxyde-water layer-bilayer capacitance. Note that at the same time the second bilayer structure is unmodiled.

At lower frequencies, modi cations also involved the oating bilayer roughness and were partially reversible. It is very di cult to determ ine which structural parameter(s) is/are responsible for the subtle modi cations observed without additional information. Nevertheless, as previously mentioned no modi cation of the silicon oxide layer was detected. The structure of the double bilayer can be well determ ined before applying the electric

eld [3], and the global structure of the bilayers (i.e. the slabs num ber and nature) seem s to be una ected by the electric eld. It thus seem ed physically reasonable to t the re ectivity curves under electric eld by varying m ainly bilayers roughness and water layers thickness; average percentages of solvent within the bilayers were also allowed to vary, accounting for the induced form ation of defects or pores in the mem branes.

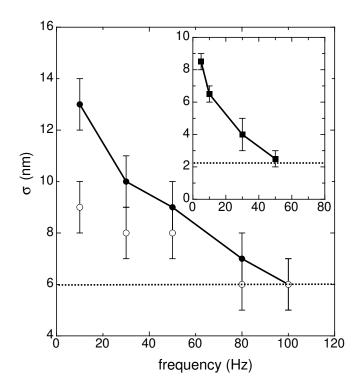


FIG.4: Top bilayer roughness vs electric eld frequency fat constant eld am plitude $V_{pp}=2 = 5V$: () DSPC double-bilayer in D_2O (in insert, () sam e curve for a DSPC bilayer); () reversibility test after each frequency (no electric eld) for the double bilayer.

W ithin this fram ework, the dominant e ect we observed was a progressive increase of the oating (top) bilayer roughness, going from 0.6 1 to 1.3 1 nm. Again it was not possible to go to lower frequencies or higher voltages to avoid substrate deterioration, and in the frequency-range studied no complete unbinding occured in D_2O .

This roughness increase seem ed to be partially reversible, as shown on gure 4. Reversibility was system atically checked in the low conductivity solution (D_2O); for beam time limitation reasons we were not able to check it in the CaC b_2 conductive solution. A small increase of the thickness of water between the bilayers $D_{w;2}$, in the limit of the resolution of the experiment, was also observed. Finally, a progressive increase of the percentage of solvent in the oating bilayer remained constant and very low. Whether this corresponds to the form ation of pores -m ade easier by the higher tension of the supported membrane, or of perm anent holes due to electrochem ical phenom ena close to the substrate is unsure. How ever the latter seem s m ore likely as this increase of the solvent content was apparently not reversible.

The irreversible e ect on the rst bilayer at frequencies > 100 Hz, as well as the reversible e ect at low frequencies, well described by an increase of the top bilayer roughness, were observed on di erent DSPC samples. Nevertheless, as we were not able to check carefully the stability of the oxide layer in these cases we do not report corresponding data in the present paper.

2. Single bilayer

In order to check the e ect of the electric eld on the rst, substrate-bound bilayer, we perform ed experiments on a single supported DSPC bilayer. Results are shown in gure 4 (insert). They showed a progressive increase of the bilayer roughness, along with an increase of membrane-substrate distance. However no modi cation of the bilayer structure was seen, and the percentage of solvent remained very low (2%), in agreement with a good-quality sample. We can thus think that, in the case of the double-bilayer, the solvent increase in the rst bilayer is correlated to the fact that it is con ned close to the substrate by the second, uctuating bilayer.

This seems consistent with the fact that when the second bilayer unbinds, the rst one relaxes away from the substrate.

IV. DISCUSSION

The results reported above clearly show that an electric eld can induce a complete destabilisation of the top bilayer of a double-bilayer at low frequency (5-10 Hz). This very abrupt destabilisation follows a reversible increase of the bilayer roughness. It is tempting to describe this roughness in terms of thermal uctuations, and we intend to do so in this section.

A. Bilayer uctuations

We consider the small thermal uctuations of a single bilayer close to a substrate. Using common notations (see [18] for example), we note r = (x;y) the in plane coordinates and z the coordinate normal to the substrate and we call u(r) = u(x;y) the membrane position. Classical Helfrich's Ham iltonian [19] can then be written at rst order expansion in membrane's curvature as :

$$H [u(\mathbf{r})] = \int_{S}^{Z} d^{2}\mathbf{r} U (u(\mathbf{r})) + \frac{1}{2} (u(\mathbf{r}))^{2} + f'u(\mathbf{r})^{2} : \qquad (2)$$

where is the bending modulus of the bilayer, its surface tension and U the mem brane-substrate interaction potential. Using a quadratic approximation for U (u(r)) it is possible to apply the equipartition theorem for small uctuations:

$$j\mu_{q}j^{2} = \frac{1}{S} - \frac{k_{B}T}{U^{0} + q^{2} + q^{4}}$$
 (3)

Note that this expression is only valid when the uctuation amplitude is smaller than the mean distance to the substrate, which seems to be the case in our experiments. For large uctuations one would have to take into account the reduction of entropy caused by the substrate, leading to the so-called Helfrich repulsion [2, 18].

In their recent paper, Sens and Isam bert [10] describe the case of a free m em brane far from a substrate (U⁰⁰ = 0) and take into account the e ect of hydrodynam ics on the bilayer destabilisation. In particular, they showed that energy dissipation by solvent ow (viscosity) and by monolayer monolayer friction (friction coe cient b_r) lead to the selection of a fastest-destabilised m ode of wavelength q²:

$$q^{2} = \frac{(el)}{b_{fr}^{2}} / 1 m^{1}$$
 (4)

This length scale is in good agreement with the caracteristic size of vesicles prepared by electroformation.

In our experimental study, the two bilayers are not free but interact with the substrate and the other bilayer. Bilayer equilibrium position without electric eld is thus given by a competition between hydratation repulsive forces and van der W aals attractive ones, as described in ref.[2, 18]. U sing Eq. 3, it is possible to calculate the rm s amplitude of uctuations 2 :

$${}^{2} = {}^{D} z (r)^{2} = \frac{1}{(2)^{2}} {}^{Z} d^{2}q j \mu_{q} j^{2}$$
$$= \frac{k_{B} T}{2} \log \frac{q_{2}}{q_{1}}$$
(5)

with $= {}^{2} 4U^{00}$, $q_{1}^{2} = \frac{p}{2}$ and $q_{2}^{2} = \frac{+p}{2}$.

At the linear order, the e ect of an electric eld on the mem brane can be expressed as a negative surface tension e_{l} (with $e_{l} > 0$). Following the notations of ref. [10], e_{l} can be written as:

$$el = {}_{m} E_{m}^{2}$$
(6)

where $_{\rm m}$ is the mem brane dielectric constant, $E_{\rm m}$ is the local electric eld and the bilayer thickness. This negative surface tension induces enhanced therm all uctuations that can be described by replacing by $\sim = _{\rm el}$ in equation 3. Figure 5 shows the variation of as a function of the global surface tension $_{\rm el}$; here we have taken ' $40k_{\rm B}$ T and U⁰' 10^{13} Jm⁴, which are classical values for a D SPC bilayer in the uid phase 20].

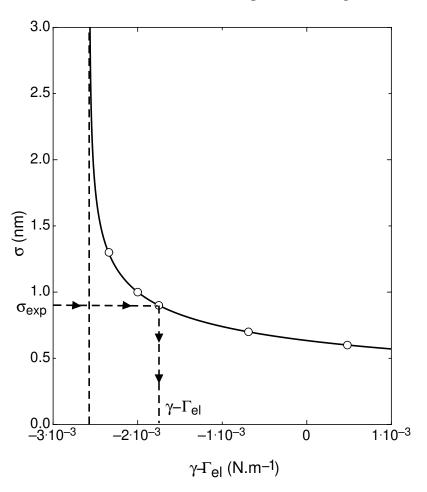


FIG.5: Mem brane rms uctuation amplitude as a function of global surface tension e_1 , deduced from equation 5. (): values probed during the experiments.

M em brane uctuations undergo a sharp divergence for a nite negative value of $c = \sqrt[4]{U^{0}}$ which is the signature of bilayer destabilisation. This unbinding occurs in a very narrow surface tension range, which could explain the abrupt destabilisation observed in our experiments.

Let us now try to evaluate the electric surface tension equivalent to the eld we have applied. It is possible to derive values of $_{el}$ using equation 5, if we know , , and U^{00} . We measured experimentally. Previous X-ray o -specular experiments 20 have shown on very similar samples (a uid D SPC bilayer deposited on an hybrid O T S-D SPC bilayer) that ' 40 k_B T and ' 0.5 m N m⁻¹. Using these experimental results we can x U^{00} to obtain the correct experimental value of measured without any electric eld. Following this method we obtain U^{00} ' 10^{13} J m⁻⁴. This value is in good agreement with theoretical estimations using a van der W aals potential [2]. It is then possible by using equation 5 to derive numerical values of $_{el}$ for the dimension elds applied, which are reported on gure 5.

Following ref. [10], the electrostatic surface tension $_{el}$ (Eq. 6) can be related to the electric eld E applied to the whole cell by:

$$e^{1} m \frac{m}{s} E^{2}$$
(7)

where m^1 and s^1 are respectively the mem brane and solvent conductivity. With $m' 2_0$, $s^1 = 0.34 \ 10^4 \ Sm^1$ for D_2O (measured experimental value) and $e^1 \ 10^3 \ Nm^1$ it leads to $m^1 \ 3 \ 10^{10} \ Sm^1$ (equivalent to a mem brane resistance $R_m \ 0.2 \ Mm^2$), in good agreement with the value obtained by Purrucker et al. [21]. In the high conductivity solution (C aC l_2 , $s^1 = 16 \ 10^4 \ Sm^1$), even if we found no value of the mem brane conductivity reported in literature, it seems clear that we are well above the unbinding surface tension c.

Field frequency seems to be an important parameter in membrane destabilisation. We were not able to detect any modi cation (reversible or irreversible) of the bilayer above 100 Hz whereas the elect becomes important below 10 Hz (Fig. 4 and 7). This is in good agreement with previous observations by Constantin et al. [11]. It is also precisely the frequency range used in electroformation techniques. In order to understand more quantitatively this elect, let us try to estimate the local electric eld acting on the bilayer. We can do so by using a simple equivalent circuit to represent the experimental set-up (gure 6).

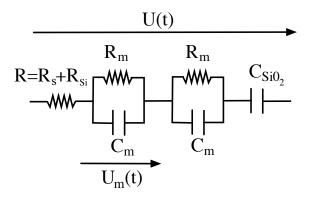


FIG.6: A simple equivalent circuit for the system .

The bilayer impedance Z_m is modelled by a resistance R_m and a capacitance C_m in parallel [21]. The substrate is described by a resistance R_{Si} (1) and a capacitance attributed to the silicon oxide C_{Si0_2} ('30 F for a 1 nm -thick oxide) in series. The electrolyte solution has a resistance R_s ('92 k for D_2O). It is then easy to derive the negative electrostatic surface tension acting on the bilayer:

$$e^{1} = \frac{1}{2} m \frac{R_{m}}{R} \frac{2}{2} \frac{U_{0}^{2}}{(1 + \frac{1}{2} m - \frac{1}{2})^{2} + \frac{1}{2} (m + \frac{1}{2} (1 + n - \frac{1}{2})^{2})^{2}}$$

where n is the number of bilayer(s), R the total resistance $R = R_s + R_{Si}$, $= \frac{R_m}{R}$ and we have introduced the two characteristic times $m = R_m C_m$ and $i = RC_{SiO_2}$.

U sing $R_s = 92 \text{ k}$ and $C_{\text{SiO}_2} = 30 \text{ F}$ as xed values, the best t to the data gives $R_n = 48 \text{ 1 k}$ (0:78 0.2 M cm²) and $C_m = 0.1 \text{ 0.01 F}$ (0.01 0.005 F cm²). The corresponding result is plotted gure 7. The value of R_m is in very good agreement with typical values of bilayer mem branes resistance, around 0.9-1 M cm² for a high coverage of the substrate (see for example Ref. [21, 22]). However the value of C_m is surprisingly lower than values

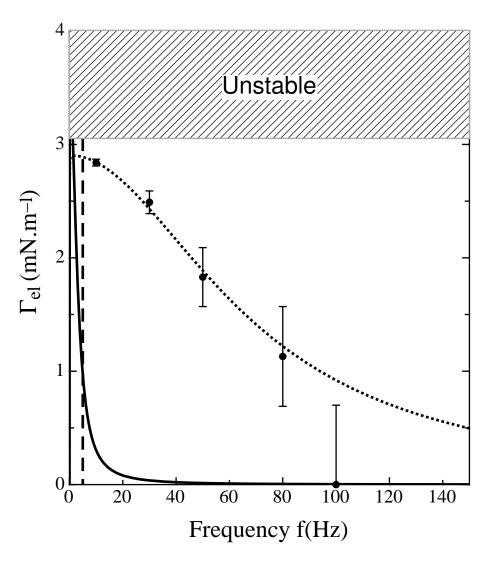


FIG.7: e_1 as a function of frequency: () values derived from experimental data; dashed line = best t using equation 8; full line = equation 8 with $R_m = 60 \text{ k}$ and $C_m = 2 \text{ F.W}$ e have represented by a dashed line the frequency limit (f 5 Hz) were silicon oxidation is observed.

usually found for supported bilayers ($0.5 \text{ F} \text{ cm}^2$ [21, 22]). We have no explanation for this disagreement. M any e ects could account for it, including the fact that the rst membrane might be damaged by the eld. M aybe our model is then too simple to give a good description of the system capacitive behaviour. We have drawn on gure 7 the curve obtained with a more consistent value of the membrane capacitance. In any case, we can notice that the frequency behaviour we observe is similar to previous observations by C onstantin and cow orkers [11].

V. CONCLUSIONS AND PERSPECTIVES

In this work we have reported the e ect of an alternative electric eld on lipid double bilayers adsorbed on doped silicon substrates, as studied by neutron re ectivity. We clearly show that the electric eld can lead to a complete unbinding of the oating bilayer in a high conductivity solution at low frequency. In a low conductivity solution, sm all reversible modi cations of the re ectivity pro les are observed and described as changes of the rm s roughness of the oating bilayer. These data could be interpreted with a uctuation spectrum including a negative electrostatic surface tension term as suggested by ref. [10]. Electric eld frequency seems to be an important parameter as no e ect is observed above 100 Hz. This result is also consistent with previous observations [1]. We have tried to understand this e ect with a simple electrokinetic model of the cell.

However, so far our results provide no information on the lateral length scale $(q^2 \text{ in ref. [10]})$ of the instability, which is one of the main predictions of the theoretical model [10]. We only measure the integrated root-mean-square amplitude of uctuations. In a near futur, we plan to perform o -specular rectivity experiments, as described in ref. [20]. They could provide important information concerning the lateral length scale (s) of the changes involved, and will enable direct measurement of the uctuation spectrum and the surface tension.

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TABLE I: Structural parameter of a DSPC double bilayer in D_2O before any electric eld is applied: (sld) = scattering length densities in 10⁶ A²; thicknesses and roughnesses in A.All values are obtained from the best t (gure 2).

					-										-			
	Silicon oxide		Solvent		H ead		Chains		H ead		Solvent		H ead		Chains		H ead	
thickness	11	1	3	0.5	6	1	36	1	6	1	19	0.5	6	1	36	1	6	1
sld	3.4	0.1	0		2.05	0.1	-0.6	0.05	2.05	0.1		0	2.05	0.1	-0.6	0.05	2.05	0.1
% solvent	1	1	1	00	19	3	2	1	19	3	1	00	19	3	2	1	19	3
roughness	3	0.5	2	1	3	1	4	1	3	1	5	1	3	1	6	1	3	1

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